

2' Pub B' 1. (Amended) A method for producing a semiconductor device comprising:  
forming an opening by etching process using a resist pattern as a mask in a multi-layered film including a nitride etching stop film, a first organic insulating film, a first oxide etching stop film and a second organic insulating film being layered in this order such that the opening penetrates from the second organic insulating film to the first organic insulating film,  
wherein a second oxide etching stop film is formed between the resist pattern and the second organic insulating film to protect the second organic insulating film from being etched during the formation of the opening.

Please add the following new claims:

10. (New) A method for producing a semiconductor device comprising:  
forming an opening by etching process using a resist pattern as a mask in a multi-layered film including an etching stop film, a first organic insulating film, another etching stop film and a second organic insulating film being layered in this order such that the opening penetrates from the second organic insulating film to the first organic insulating film,  
wherein an additional etching stop film is formed between the resist pattern and the second organic insulating film to protect the second organic insulating film from being etched during the formation of the opening, and